

N-Channel 200-V (D-S) MOSFET

Key Features:

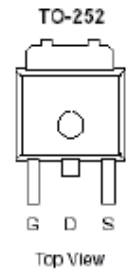
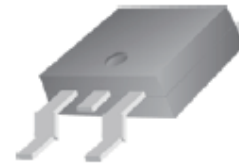
- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

Typical Applications:

- PoE Power Sourcing Equipment
- PoE Powered Devices
- Telecom DC/DC converters
- White LED boost converters



RoHS
COMPLIANT
HALOGEN
FREE



PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (m Ω)	I_D (A)
200	400 @ $V_{GS} = 10V$	9.2
	450 @ $V_{GS} = 5.5V$	8.7

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	200	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	9.2	A
Pulsed Drain Current ^b		I_{DM}	50	
Continuous Source Current (Diode Conduction)		I_S	45	A
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	50	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a		$R_{\theta JA}$	50	$^\circ\text{C/W}$
Maximum Junction-to-Case		$R_{\theta JC}$	3	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

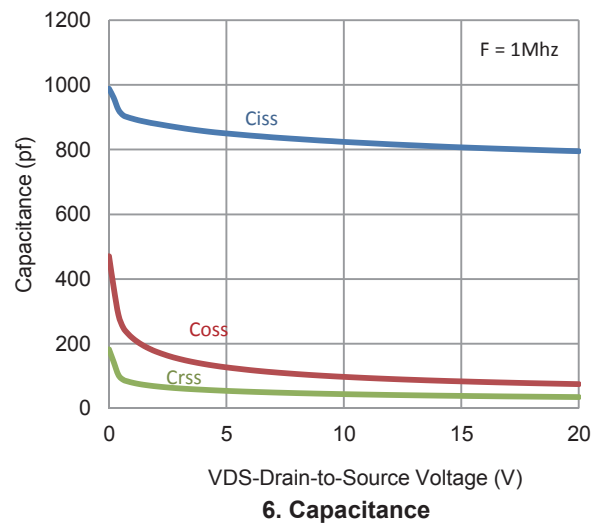
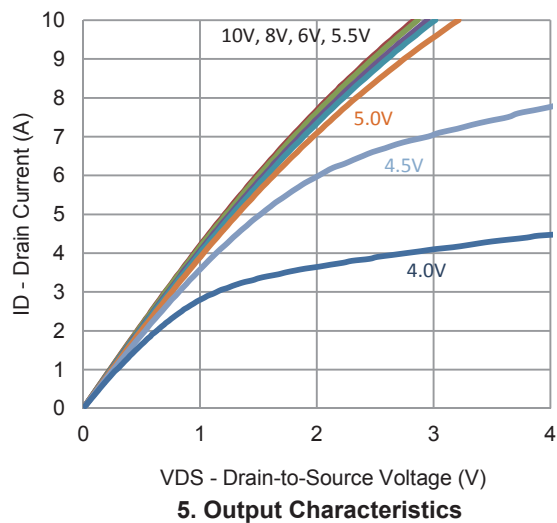
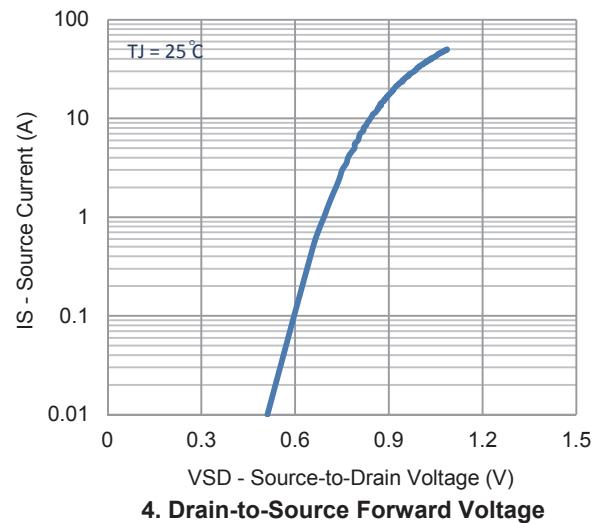
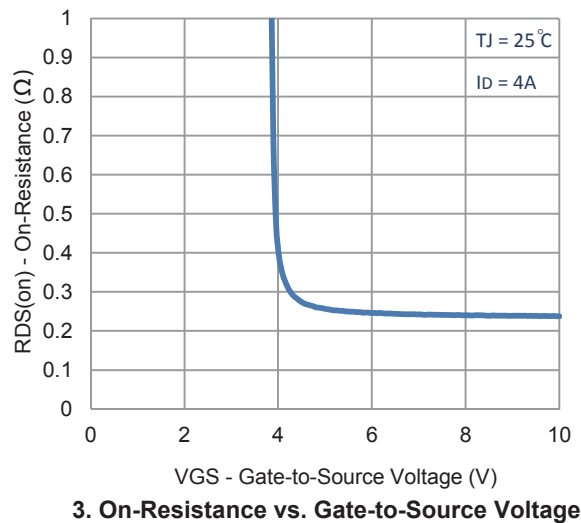
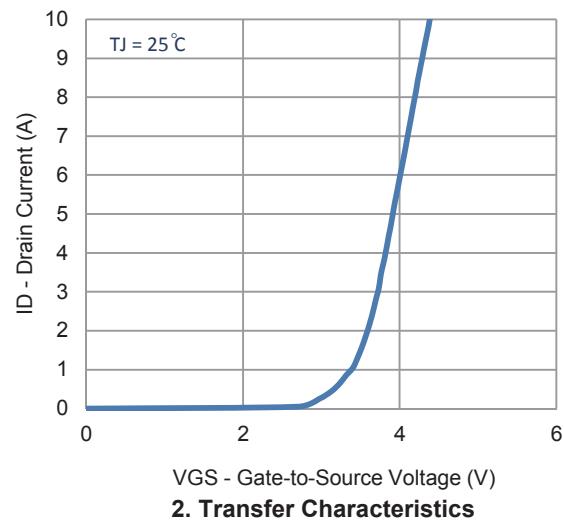
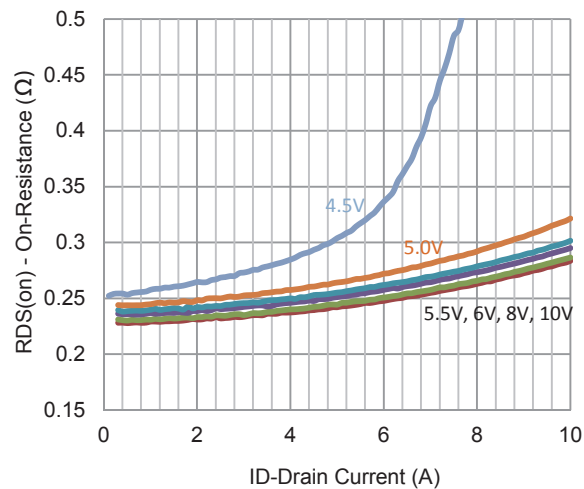
Typical Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1		3.5	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V$, $V_{GS} = 20 V$			± 10	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 160 V$, $V_{GS} = 0 V$			1	μA
		$V_{DS} = 160 V$, $V_{GS} = 0 V$, $T_J = 55^\circ C$			25	
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 V$, $V_{GS} = 10 V$	34			A
Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS} = 10 V$, $I_D = 4 A$			400	$m\Omega$
		$V_{GS} = 5.5 V$, $I_D = 3.5 A$			450	
Forward Transconductance	g_{fs}	$V_{DS} = 15 V$, $I_D = 4 A$		10		S
Diode Forward Voltage	V_{SD}	$I_S = 23 A$, $V_{GS} = 0 V$		0.95		V
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = 100 V$, $V_{GS} = 5.5 V$, $I_D = 4 A$		9.1		nC
Gate-Source Charge	Q_{gs}			3.8		
Gate-Drain Charge	Q_{gd}			3.8		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100 V$, $R_L = 5 \Omega$, $I_D = 4 A$, $V_{GEN} = 10 V$, $R_{GEN} = 6 \Omega$		3.7		nS
Rise Time	t_r			7.7		
Turn-Off Delay Time	$t_{d(off)}$			26.3		
Fall Time	t_f			12.4		
Input Capacitance	C_{iss}	$V_{DS} = 15 V$, $V_{GS} = 0 V$, $f = 1 MHz$		807		pF
Output Capacitance	C_{oss}			81		
Reverse Transfer Capacitance	C_{rss}			38		

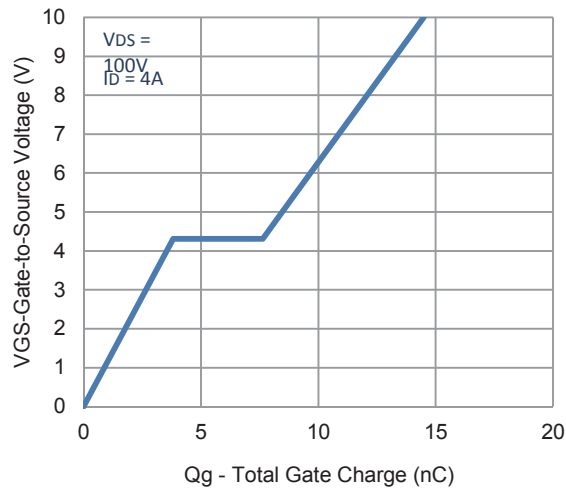
Notes

- Pulse test: $PW \leq 300 \mu s$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

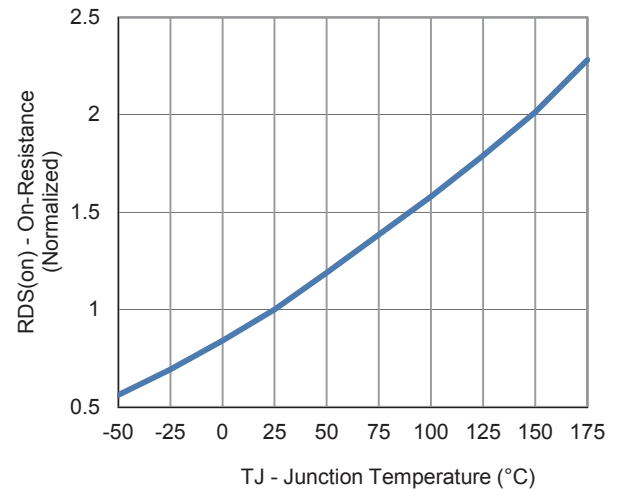
Typical Electrical Characteristics



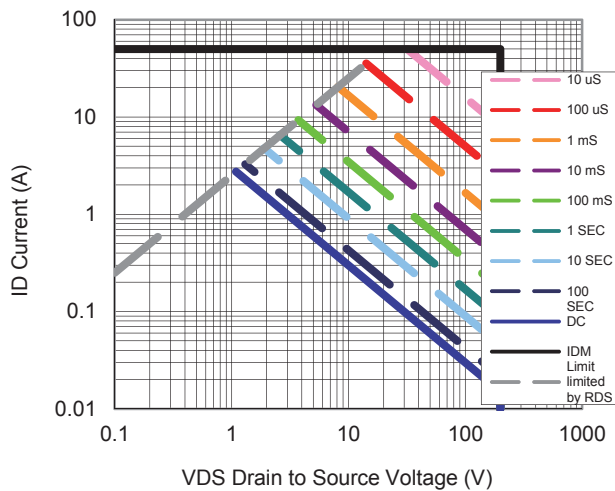
Typical Electrical Characteristics



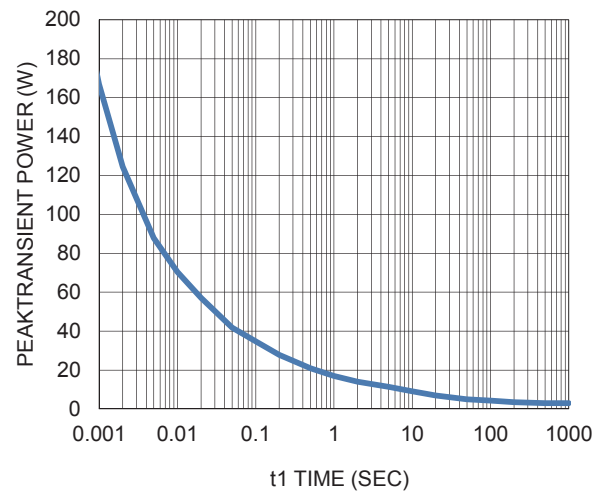
7. Gate Charge



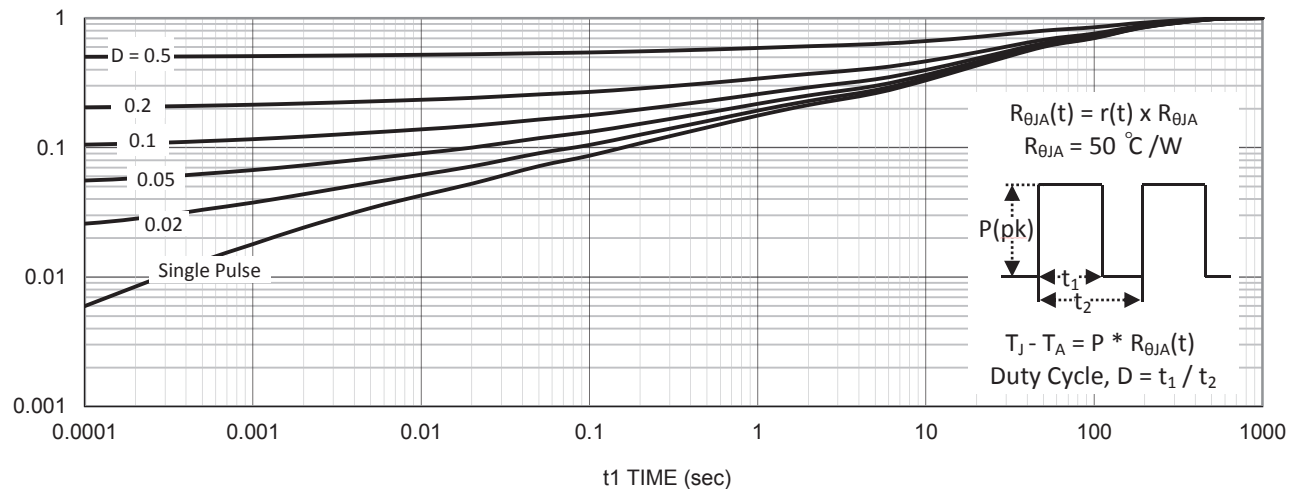
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

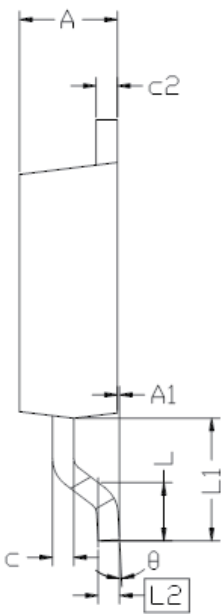
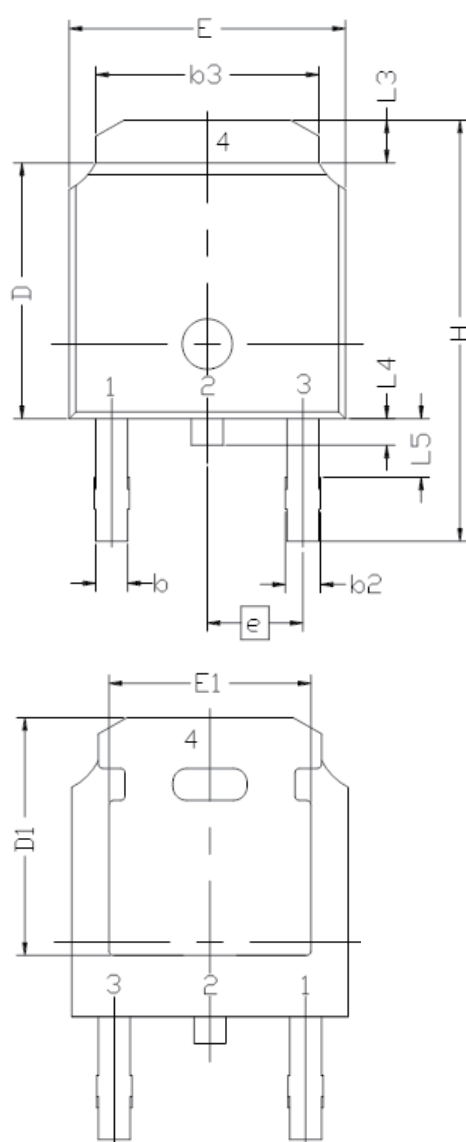


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2.743 REF		
L2	0.508 BSC		
L3	0.89	--	1.27
L4	0.64	--	1.01
L5	--	--	--
D	6.00	6.10	6.223
H	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2.286 BSC		
A	2.20	2.30	2.38
A1	0	--	0.127
c	0.45	0.50	0.60
c2	0.45	0.50	0.58
D1	5.30	--	--
E1	4.40	--	--
theta	0°	--	10°

- Note:
- 1. All Dimension Are In mm.
 - 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
 - 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.